EPS13D2C1HG-48.750M



EPS13D2 C 1 H G -48.750M

Series — RoHS Compliant (Pb-free) 3.3V 4 Pad 5mm x 7mm Ceramic SMD LVCMOS Programmable Spread Spectrum Oscillator Nominal Frequency 48.750MHz

-0.50% Down Spread

- Output Control Function Tri-State

> Duty Cycle -50 ±10%

ELECTRICAL SPECIFICATIONS Nominal Frequency 48.750MHz

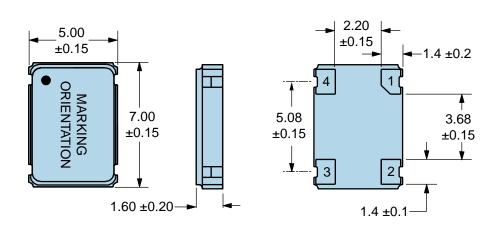
Aging at 25°CAging at 25°C, Shock, and Vibration.)Aging at 25°C±5ppm First Year MaximumSupply Voltage3.3Vdc ±0.3VdcMaximum Supply Voltage-0.5Vdc to +7.0VdcInput Current30mA Maximum (Unloaded; Vdd=3.3Vdc)Output Voltage Logic High (Voh)Vdd-0.4Vdc Minimum (IOH=-8mA)Output Voltage Logic Low (Vol)0.4Vdc Maximum (IOL=+8mA)Rise/Fall Time2.7nSec Maximum (Measured at 20% to 80% of Waveform)Duty Cycle50 ±10% (Measured at 50% of Waveform)Load Drive Capability15pF MaximumOutput Control FunctionTri-State (High Impedance Internal Pull Down Resistor of 100kOhms Typical on Pad 3, Internal Pull Up Resistor of 100kOhms Typical on Pad 1)Tri-State Output Disable Time350nSec MaximumTri-State Output Disable Time350nSec Maximum	Nominal Trequency	
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Rise/Fall Time 2.7nSec Maximum (Measured at 20% to 80% of Waveform) Duty Cycle 50 ±10% (Measured at 50% of Waveform) Load Drive Capability 15pF Maximum Output Logic Type CMOS Output Control Function Tri-State (High Impedance Internal Pull Down Resistor of 100kOhms Typical on Pad 3, Internal Pull Up Resistor of 100kOhms Typical on Pad 1) Tri-State Input Voltage (Vih and Vil) 70% of Vdd Minimum or No Connection to Enable Output, 30% of Vdd Maximum to Disable Output Tri-State Output Disable Time 350nSec Maximum Tri-State Output Enable Time 350nSec Maximum	Output Voltage Logic High (Voh)	Vdd-0.4Vdc Minimum (IOH=-8mA)
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Resistor of 100kOhms Typical on Pad 1) Tri-State Input Voltage (Vih and Vil) 70% of Vdd Minimum or No Connection to Enable Output, 30% of Vdd Maximum to Disable Output Tri-State Output Disable Time 350nSec Maximum Tri-State Output Enable Time 350nSec Maximum	Output Logic Type	CMOS
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Tri-State Output Enable Time 350nSec Maximum	Tri-State Input Voltage (Vih and Vil)	70% of Vdd Minimum or No Connection to Enable Output, 30% of Vdd Maximum to Disable Output
· · · · · · · · · · · · · · · · · · ·	Tri-State Output Disable Time	350nSec Maximum
Disable Current 20mA Maximum (Liplagdad: Bad 1-Cround: V/dd-2 2)/dc)	Tri-State Output Enable Time	350nSec Maximum
	Disable Current	20mA Maximum (Unloaded; Pad 1=Ground; Vdd=3.3Vdc)
Spread Spectrum -0.50% Down Spread	Spread Spectrum	-0.50% Down Spread
Modulation Frequency 30kHz Minimum, 31.5kHz Typical, 33kHz Maximum	Modulation Frequency	30kHz Minimum, 31.5kHz Typical, 33kHz Maximum
Period Jitter 400pSec Maximum (Cycle to Cycle; Spread Spectrum-On; Vdd=3.3Vdc)	Period Jitter	400pSec Maximum (Cycle to Cycle; Spread Spectrum-On; Vdd=3.3Vdc)
Start Up Time 10mSec Maximum	Start Up Time	10mSec Maximum
Storage Temperature Range -55°C to +125°C	Storage Temperature Range	-55°C to +125°C

ENVIRONMENTAL & MECHANICAL SPECIFICATIONS

Fine Leak Test	MIL-STD-883, Method 1014, Condition A
Gross Leak Test	MIL-STD-883, Method 1014, Condition C
Mechanical Shock	MIL-STD-202, Method 213, Condition C
Resistance to Soldering Heat	MIL-STD-202, Method 210
Resistance to Solvents	MIL-STD-202, Method 215
Solderability	MIL-STD-883, Method 2003
Temperature Cycling	MIL-STD-883, Method 1010
Vibration	MIL-STD-883, Method 2007, Condition A

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MECHANICAL DIMENSIONS (all dimensions in millimeters)



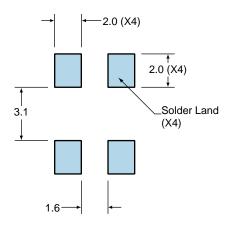
PIN	CONNECTION
1	Tri-State
2 3	Case/Ground
3	Output
4	Supply Voltage
LINE	MARKING
LINE	MARKING
1	ECLIPTEK
2 3	48.750M

ECLIPIEK CORPORATION

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Suggested Solder Pad Layout

All Dimensions in Millimeters



All Tolerances are ±0.1

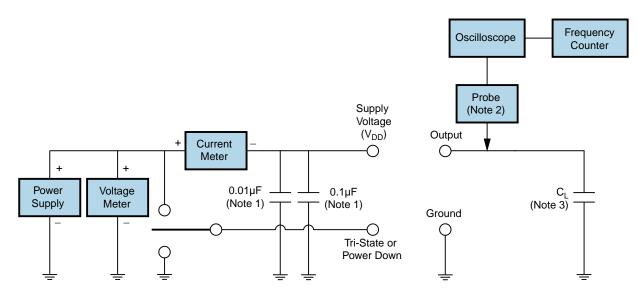
EPS13D2C1HG-48.750M



OUTPUT WAVEFORM & TIMING DIAGRAM



Test Circuit for CMOS Output



Note 1: An external 0.1μ F low frequency tantalum bypass capacitor in parallel with a 0.01μ F high frequency ceramic bypass capacitor close to the package ground and V_{DD} pin is required.

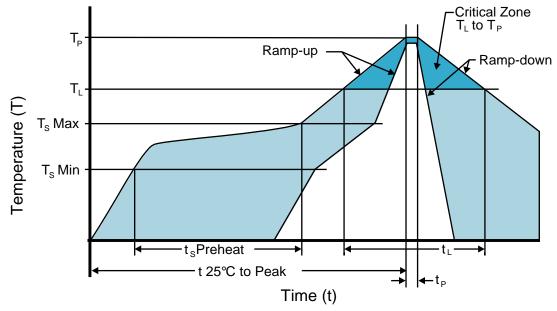
Note 2: A low capacitance (<12pF), 10X attenuation factor, high impedance (>10Mohms), and high bandwidth (>300MHz) passive probe is recommended.

Note 3: Capacitance value \dot{C}_L includes sum of all probe and fixture capacitance.



Recommended Solder Reflow Methods

EPS13D2C1HG-48.750M



High Temperature Infrared/Convection

T_s MAX to T_L (Ramp-up Rate)	3°C/second Maximum
Preheat	
- Temperature Minimum (T _s MIN)	150°C
- Temperature Typical (T _s TYP)	175°C
- Temperature Maximum (T _s MAX)	200°C
- Time (t _s MIN)	60 - 180 Seconds
Ramp-up Rate (T⊾ to T _P)	3°C/second Maximum
Time Maintained Above:	
- Temperature (T∟)	217°C
- Time (t∟)	60 - 150 Seconds
Peak Temperature (T _P)	260°C Maximum for 10 Seconds Maximum
Target Peak Temperature (T _P Target)	250°C +0/-5°C
Time within 5°C of actual peak (t_p)	20 - 40 seconds
Ramp-down Rate	6°C/second Maximum
Time 25°C to Peak Temperature (t)	8 minutes Maximum
Moisture Sensitivity Level	Level 1



Recommended Solder Reflow Methods

EPS13D2C1HG-48.750M



Low Temperature Infrared/Convection 240°C

T _s MAX to T _L (Ramp-up Rate)	5°C/second Maximum
Preheat	
- Temperature Minimum (Ts MIN)	N/A
- Temperature Typical (T _s TYP)	150°C
- Temperature Maximum (T _s MAX)	N/A
- Time (t _s MIN)	60 - 120 Seconds
Ramp-up Rate (T⊾ to T _P)	5°C/second Maximum
Time Maintained Above:	
- Temperature (T∟)	150°C
- Time (t∟)	200 Seconds Maximum
Peak Temperature (T _P)	240°C Maximum
Target Peak Temperature (T _P Target)	240°C Maximum 1 Time / 230°C Maximum 2 Times
Time within 5°C of actual peak (t _p)	10 seconds Maximum 2 Times / 80 seconds Maximum 1 Time
Ramp-down Rate	5°C/second Maximum
Time 25°C to Peak Temperature (t)	N/A
Moisture Sensitivity Level	Level 1

Low Temperature Manual Soldering

185°C Maximum for 10 seconds Maximum, 2 times Maximum.

High Temperature Manual Soldering

260°C Maximum for 5 seconds Maximum, 2 times Maximum.